

4Q Triac

Rev. 03 — 4 April 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications.

1.2 Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

1.3 Applications

General purpose motor control

General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see Figure 4; see Figure 5	-	-	25	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	4	Α
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ constant of } T}$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ c}}$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	30	70	mA



4Q Triac

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N 1
2	T2	main terminal 2	mb	T2T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2	1 2 3	
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT136-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78
BT136-600/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

Limiting values

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	4	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	25	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	27	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	3.1	A^2s
dl _T /dt	rate of rise of on-state current	$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+G+$	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+G$ -	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G-	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

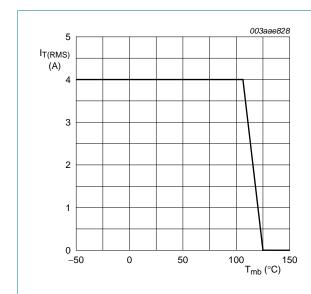
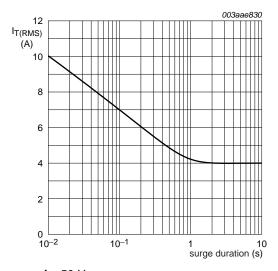


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



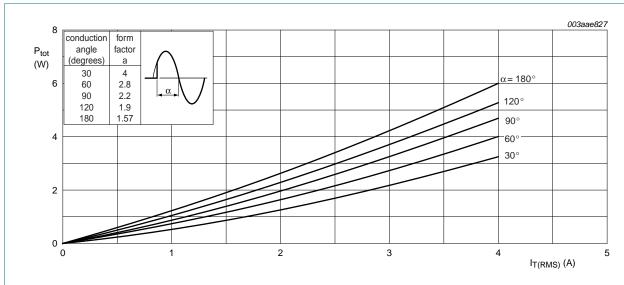
f = 50 Hz $T_{mb} \le 107 \, ^{\circ}C$

Fig 2. RMS on-state current as a function of surge duration; maximum values

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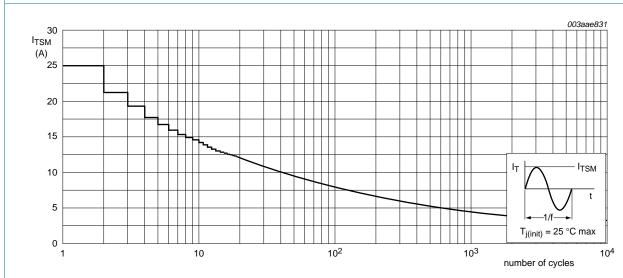
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 α = conduction angle

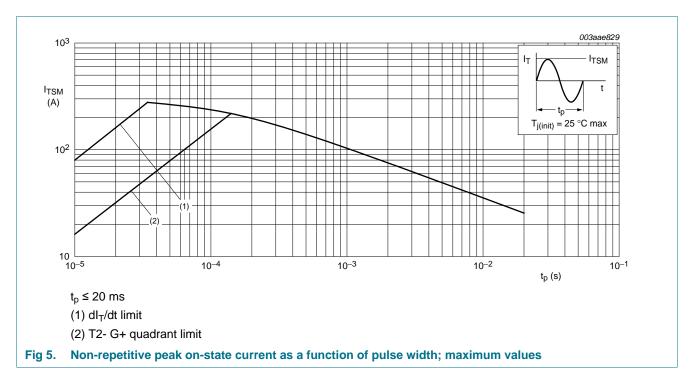
Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

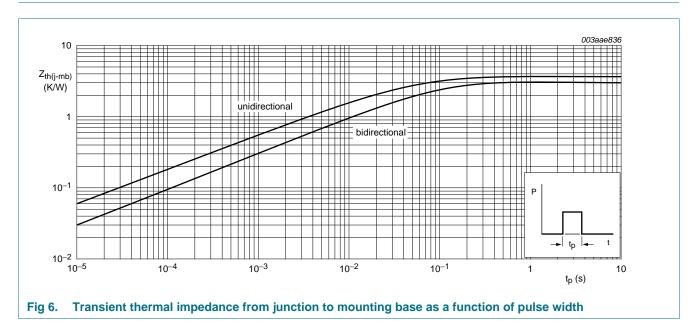
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from	half cycle; see Figure 6	-	-	3.7	K/W
	junction to mounting base	full cycle; see Figure 6	-	-	3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



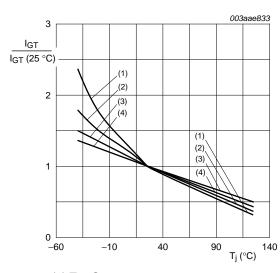
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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-};$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	30	70	mA
I <u>L</u>	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	7	20	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	16	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	5	20	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	7	30	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	5	15	mΑ
V _T	on-state voltage	$I_T = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{Model of the content of the content$	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	$V_D = 600 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit	100	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C};$ $dI_{com}/dt = 1.8 \text{ A/ms}; I_T = 4 \text{ A}; \text{ gate open}$ circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ mA};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

4Q Triac



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

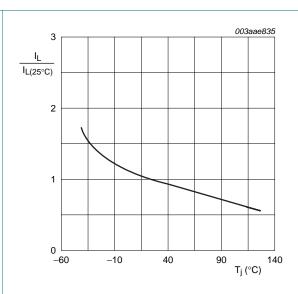


Fig 8. Normalized latching current as a function of junction temperature

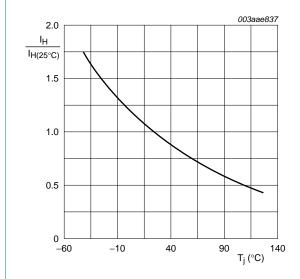
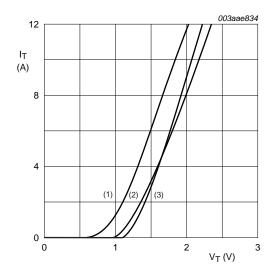


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}$

 $R_s = 0.091 \Omega$

(1) T_j = 125 °C; typical values

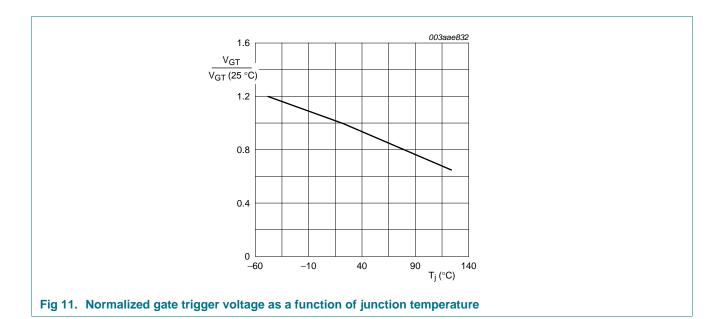
(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

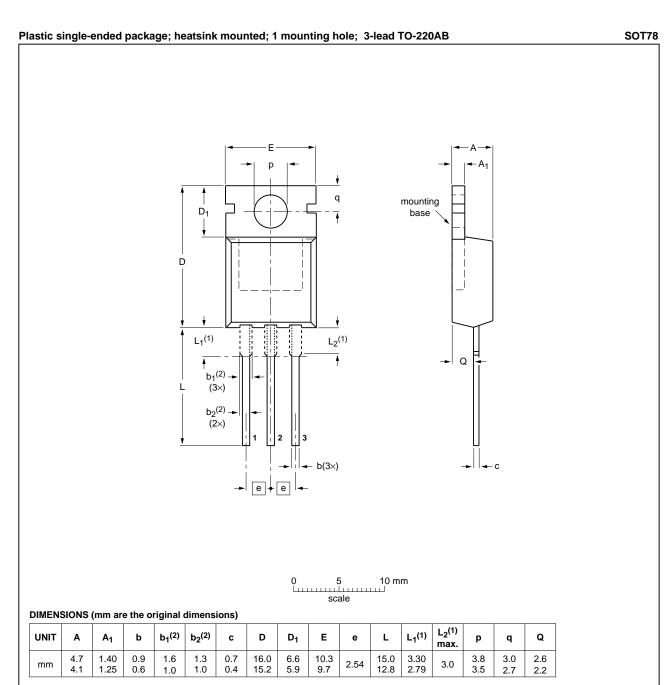
Fig 10. On-state current as a function of on-state voltage

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7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE D	ISSUE DATE		
VERSION	N IEC JEDEC		IEC JEDEC JEITA		JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13		

Fig 12. Package outline SOT78 (TO-220AB)

BT136-600

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BT136-600

4Q Triac

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BT136-600 v.3	20110404	Product data sheet	-	BT136_SERIES v.2	
Modifications:	 The format of of NXP Semic 	of this data sheet has been redesigned to comply with the new identity guideline miconductors.			
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.	
	 Type number 	BT136-600 separated from o	lata sheet BT136 SERI	ES v.2.	
BT136_SERIES v.2	20010601	Product specification	-	BT136_SERIES v.1	

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information

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